



IXTH3N120 Information



For Reference Only

Part Number IXTH3N120

Manufacturer IXYS

Category Discrete Semiconductor Products

Transistors - FETs, MOSFETs - Single

Description MOSFET N-CH 1200V 3A TO-247

Package TO-247-3

For the pricing/inventory/lead time, please contact

us

Website: https://www.heisener.com E-mail: salesdept@heisener.com



Request a Quote

Certified Quality

Heisener's commitment to quality has shaped our processes for sourcing, testing, shipping, and every step in between. This foundation underlies each component we sell.









IXTH3N120 Specifications

Manufacturer Part Number	IXTH3N120
Manufacturer	IXYS
Category	Discrete Semiconductor Products
	Transistors - FETs, MOSFETs - Single
Package	TO-247-3
Series	-
FET Type	N-Channel
Technology	MOSFET (Metal Oxide)
Drain to Source Voltage (Vdss)	1200V
Current - Continuous Drain (Id) @ 25°C	3A (Tc)
Drive Voltage (Max Rds On, Min Rds On)	10V
Vgs(th) (Max) @ Id	4.5V @ 250μA
Gate Charge (Qg) (Max) @ Vgs	39nC @ 10V
Input Capacitance (Ciss) (Max) @ Vds	1300pF @ 25V
Vgs (Max)	±20V
FET Feature	-
Power Dissipation (Max)	200W (Tc)
Rds On (Max) @ Id, Vgs	4.5 Ohm @ 500mA, 10V
Operating Temperature	-55°C ~ 150°C (TJ)
Mounting Type	Through Hole
Supplier Device Package	TO-247 (IXTH)
Package / Case	TO-247-3
	Report errors?

IXTH3N120 Guarantees



Quality Guarantees

We provide 90 days warranty. *

If the items you received were not in perfect quality, we would be responsible for your refund or replacement, but the items must be returned in their original condition.



Service Guarantees

We guarantee 100% customer satisfaction.

Our experienced sales team and tech support team back our services to satisfy all our customers.

IXTH3N120 Payment Methods



















IXTH3N120 Shipping Methods













If you have any question about IXTH3N120, please do not hesitate to contact us!

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